



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application No. 09/833,078) Art Unit 2814
Filed April 12, 2001) Examiner: W. Louie
Confirmation No. 1456) Attorney Docket No.:
Inventors: David A. THOMPSON et al) 115354-00116
(formerly 45-35)
For: METHOD FOR LOCALLY MODIFYING)
THE EFFECTIVE BANDGAP ENERGY)
IN INDIUM GALLIUM ARSENIDE)
PHOSPHIDE (InGaAsP) QUANTUM)
WELL STRUCTURES)

October 3, 2002

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AMENDMENT

Hon Commissioner for Patents
Box Non-Fee Amendment
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 3, 2002, please amend the above-captioned patent application as follows:

In the claims:

Kindly cancel claims 17-21 without prejudice to the subject matter thereof.

Please add the following new claims:

AI
--22. (New) A method as defined in claim 14, wherein the reduced temperature MBE process is performed at a temperature of 300°C.

23. (New) A method as defined in claim 15, wherein the thickness of the grown Indium Phosphide layer is not greater than 1000Å.

24. (New) A method as defined in claim 1, wherein the first Indium Phosphide layer has a thickness not greater than 400Å.--